

## RJK5020DPK

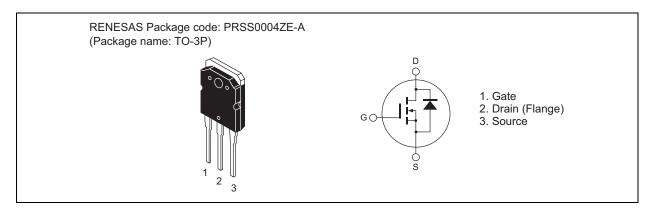
# Silicon N Channel MOS FET High Speed Power Switching

REJ03G1263-0200 Rev.2.00 Dec 19, 2006

### **Features**

- Low on-resistance
- Low leakage current
- High speed switching

### **Outline**



### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

| Item  | Symbol                       | Ratings     | Unit |
|---|------------------------------|-------------|------|
| Drain to source voltage                     | $V_{DSS}$                    | 500         | V    |
| Gate to source voltage                      | $V_{GSS}$                    | ±30         | V    |
| Drain current                               | I <sub>D</sub>               | 40          | А    |
| Drain peak current                          | I <sub>D (pulse)</sub> Note1 | 120         | Α    |
| Body-drain diode reverse drain current      | I <sub>DR</sub>              | 40          | Α    |
| Body-drain diode reverse drain peak current | I <sub>DR</sub> (pulse)      | 120         | Α    |
| Avalanche current                           | I <sub>AP</sub> Note3        | 12.5        | Α    |
| Avalanche energy                            | E <sub>AR</sub> Note3        | 8.6         | mJ   |
| Channel dissipation                         | Pch Note2                    | 200         | W    |
| Channel to case thermal impedance           | θch-c                        | 0.625       | °C/W |
| Channel temperature                         | Tch                          | 150         | °C   |
| Storage temperature                         | Tstg                         | -55 to +150 | °C   |

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. Value at Tc = 25°C

3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C

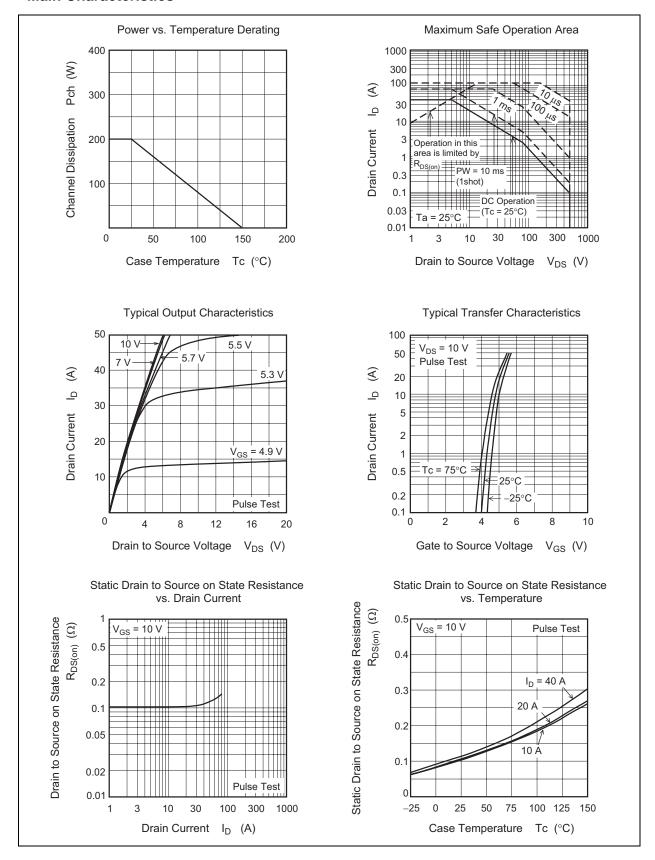
### **Electrical Characteristics**

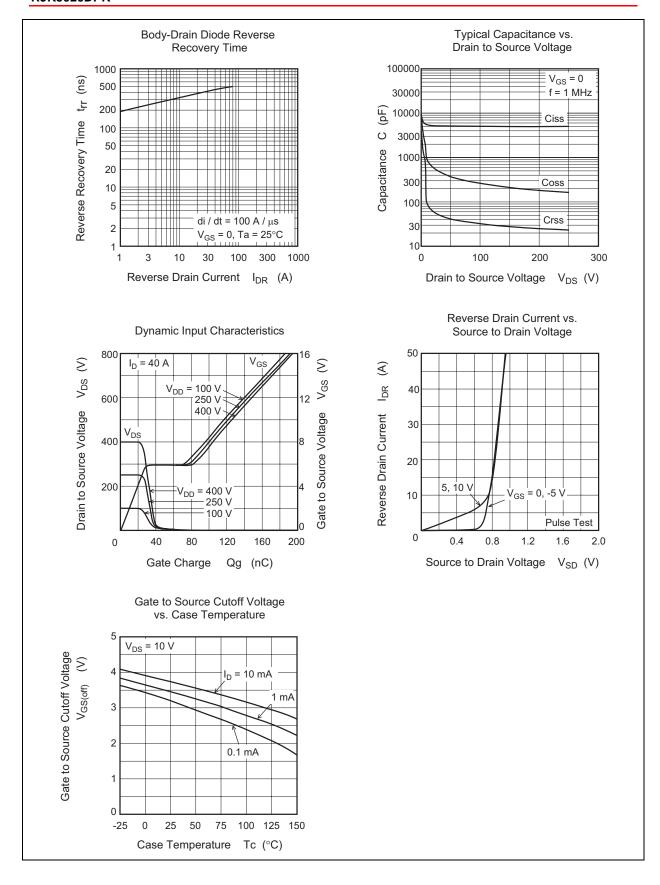
 $(Ta = 25^{\circ}C)$ 

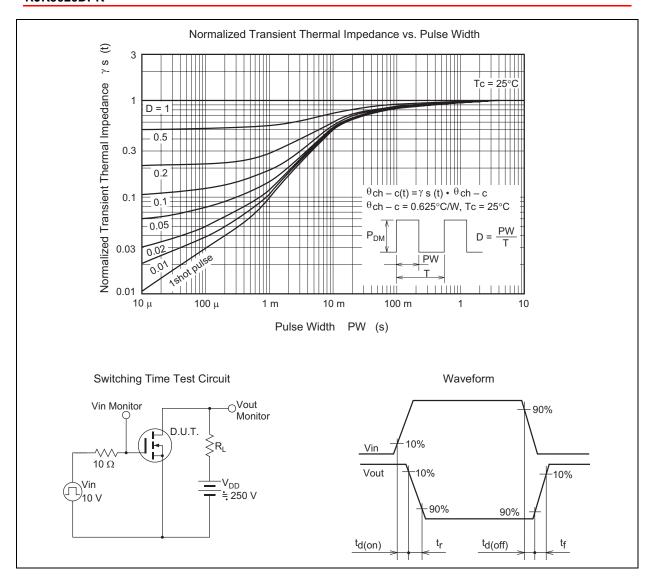
| Item                                       | Symbol              | Min | Тур   | Max   | Unit | Test conditions   |
|--|---------------------|-----|-------|-------|------|---|
| Drain to source breakdown voltage          | $V_{(BR)DSS}$       | 500 | _     | _     | V    | $I_D = 10 \text{ mA}, V_{GS} = 0$   |
| Zero gate voltage drain current            | I <sub>DSS</sub>    | _   | _     | 1     | μΑ   | $V_{DS} = 500 \text{ V}, V_{GS} = 0$  |
| Gate to source leak current                | I <sub>GSS</sub>    | _   | _     | ±0.1  | μΑ   | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$   |
| Gate to source cutoff voltage              | $V_{GS(off)}$       | 3.0 | _     | 4.5   | V    | $V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$   |
| Static drain to source on state resistance | R <sub>DS(on)</sub> | _   | 0.102 | 0.118 | Ω    | $I_D = 20 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$   |
| Input capacitance                          | Ciss                | _   | 5150  | _     | pF   | V <sub>DS</sub> = 25 V  |
| Output capacitance                         | Coss                | _   | 525   | _     | pF   | V <sub>GS</sub> = 0<br>f = 1 MHz  |
| Reverse transfer capacitance               | Crss                | _   | 55    | _     | pF   |   |
| Turn-on delay time                         | t <sub>d(on)</sub>  | _   | 52    | _     | ns   | I <sub>D</sub> = 20 A   |
| Rise time                                  | t <sub>r</sub>      | _   | 115   | _     | ns   | $\begin{aligned} V_{GS} &= 10 \text{ V} \\ R_L &= 12.5 \ \Omega \\ Rg &= 10 \ \Omega \end{aligned}$ |
| Turn-off delay time                        | t <sub>d(off)</sub> | _   | 180   | _     | ns   |   |
| Fall time                                  | t <sub>f</sub>      | _   | 125   | _     | ns   |   |
| Total gate charge                          | Qg                  | _   | 126   | _     | nC   | V <sub>DD</sub> = 400 V   |
| Gate to source charge                      | Qgs                 | _   | 26    | _     | nC   | $V_{GS} = 10 \text{ V}$<br>$I_{D} = 40 \text{ A}$   |
| Gate to drain charge                       | Qgd                 | _   | 54    | _     | nC   |   |
| Body-drain diode forward voltage           | $V_{DF}$            | _   | 0.90  | 1.50  | V    | $I_F = 40 \text{ A}, V_{GS} = 0^{\text{Note4}}$   |
| Body-drain diode reverse recovery time     | t <sub>rr</sub>     | _   | 450   | _     | ns   | $I_F = 40 \text{ A}, V_{GS} = 0$<br>$di_F/dt = 100 \text{ A}/\mu\text{s}$                           |

Notes: 4. Pulse test

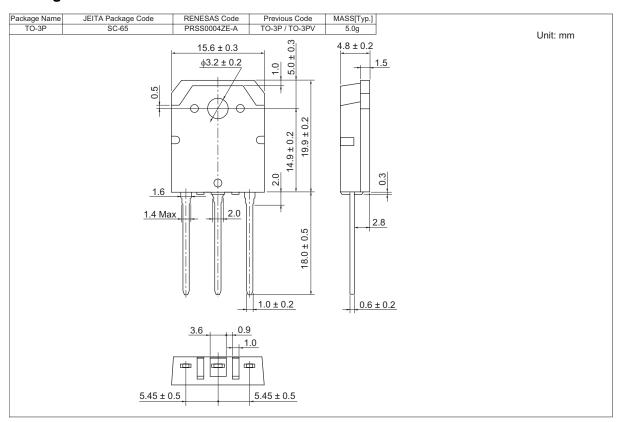
### **Main Characteristics**







### **Package Dimensions**



### **Ordering Information**

| Part No.         | Quantity | Shipping Container |
|------------------|----------|--------------------|
| RJK5020DPK-00-T0 | 360 pcs  | Box (Tube)         |

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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